Theoretical analysis of the incremental band gap and effective electron mass in $Hg_{1-x}Cd_xTe$ in the presence of light wave

Anirban Neogi, Manali Dhar, Amit Kr. Aditya

Abstract

We are going to present a simple theoretical analysis of the effective electron mass (EEM) at the Fermi level for $Hg_{1-x}Cd_xTe$ materials in the presence of light waves whose unperturbed energy bands are defined by the three-band model of Kane. The unperturbed isotropic energy spectrum in the presence of light changes into an anisotropic dispersion relation. On the other hand in the presence of light, the conduction band moves vertically upward and the band gap increases with the intensity and colors of light. It has been found, that the EEM increases with increasing electron concentration, intensity and wavelength in different manners. The effective momentum mass (EMM) at the Fermi level depend strongly on both the light intensity and wavelength. The nature of change is totally band-structure-dependent and is affected by the different energy band constants.

Index Terms

Effective Momentum Mass, Absorption coefficient, Kane Two & Three band model, Perturbation.

I. INTRODUCTION

It must be noted that among the various definitions of the effective electron mass (EEM), it is the effective momentum mass (EMM) that should be regarded as the basic quantity and this is due to the fact that it is the mass that appears in the description of transport phenomena and all other properties of the conduction electrons in a band with arbitrary band non-parabolicity[4].At present various energy wave vector dispersion relations are available which have created an interest in analyzing the EMM for ternary materials. Various variations of EMM with quantizing electric and magnetic field are available. Sometime it varies with electron concentration or sometimes with doping in heavily doped materials with the presence of band tails. It is interesting to mention that EMM oscillates with inverse quantizing magnetic fields due to SdH effect. The EMM in quantum wells and quantum wires depends on Fermi Energy and quantum numbers. However some moderate discussion about EMM for ternary materials is required.

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Anirban Neogi ,ECE Dept, Dr. Sudhir Chandra sur Degree Engineering College,Kolkata 74 Kolkata, India

Manali Dhar ECE Dept, Dr. Sudhir Chandra sur Degree Engineering College,Kolkata 74 Kolkata, India

Amit Kumar Aditya, ECE Dept, Dr. Sudhir Chandra sur Degree Engineering College,Kolkata74,Kolkata, India

We are going to use n-$Hg_{1-x}Cd_xTe$ lattice matched to InP as an example of III-V ternary compound semiconductor which is a classic narrow gap compound and an important material for optoelectronic applications whose band gap can be varied to cover a spectral range from 0.8μm-30 μm, by adjusting the alloy composition[40].In this paper we have calculated the dispersion relation of conduction electron of III-V ternary materials in presence of light-wave whose unperturbed electron energy spectrum is described in three band model of Kane. The dispersion relation for the said material in presence of external photo excitation is studied by the two band model of Kane for the purpose of the relative comparison. The expression for EMM is calculated for all the above mentioned cases.

II. THEORETICAL BACKGROUND

Electron Dispersion Law in presence of light wave in n-$Hg_{1-x}Cd_xTe$

With the application of electro magnetic field (characterizing a light wave with vector potential $(\vec{X})$ the Hamiltonian for conduction electron is given by [27]

$$\bar{H}= \frac{(\vec{p}+e\vec{X})^2}{2m_c} + V(\vec{r}) \quad (1)$$

Where $\vec{p}$ is the momentum vector, $\vec{X}$ is the vector potential, $V(\vec{r})$ is the crystal potential and m_c is the EMM in absence of any field. With reference to the standard theory of radiation, we assume $(\nabla.\vec{A})=0$ and $[\vec{p}\ , \vec{X}]=0$ and therefore equation (1) can be modified as

$$\frac{(\vec{p}+e\vec{X})^2}{2m_c} = \frac{(p^2+e(\vec{p}\cdot\vec{X}+\vec{X}.\vec{p})+X^2)}{2m_c}$$

With $|\vec{X}|^2=0$ and $\vec{p}\cdot\vec{X}=0$

$$\frac{(\vec{p}+e\vec{X})^2}{2mc}=\frac{p2}{2mc} + \frac{e.\vec{X}\vec{p}}{2mc}$$

Therefore equation (1) can be rewritten as

$$\bar{H}=\bar{H}_0+\bar{H'}\ ,$$

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where $\bar{H}_0 = \frac{p2}{2m_c} + V(\vec{r})$ (2)

and $\overline{H'} = \frac{e}{2m_c}.\ \vec{X}.\vec{p}$ (3)

Here $\overline{H'}$ represents perturbation to the unperturbed Hamiltonian $\bar{H}_0$. We can rewrite equation (3) as

$$\overline{H'} = \left(\frac{-i\bar{h}e}{2mc}\right)\ (\vec{X}.\nabla) \quad (4)$$

The vector potential ($\vec{X}$) of a plane wave can be written as

$$\vec{X} = X_0\vec{\varepsilon}_s \cos(\vec{s}_0\ .\ \vec{r} - \omega t) \quad (5)$$

Where X_0 is the amplitude of the light wave, $\vec{\varepsilon}_s$ is the polarization vector, $\vec{s}_0$ is the momentum vector of the incident photon, $\vec{r}$ is the position vector and ω is the angular frequency of light wave. From equation (4) and (5), considering initial and final state [16]

$$\overline{H'}_{nl} = \frac{e}{2m}\langle n\bar{k}|\ \vec{A}.\vec{p}\ ||\bar{q}\rangle \quad (6)$$

This in turn gives,

$$\overline{H'}_{nl} = \left(\frac{-A0i\bar{h}e}{4mc}\right).\vec{\varepsilon}_s\ .$$
$$\{\langle n\vec{k}|\exp(i\vec{s}0.\vec{r})\nabla|l\bar{q}\rangle e^{-i\omega t}\}$$
$$+\{\langle n\bar{k}|\exp(-i\vec{s}0.\vec{r})\nabla|l\vec{q}\rangle e^{i\omega t}\} \quad (7)$$

The first matrix element of equation (7) can be written as [27]

$$\langle n\vec{k}|\exp(i\vec{s}0\ .\vec{r})\nabla|l\bar{q}\rangle = \int \exp(i[\vec{q} + \vec{s}0 - \vec{k}].\ \vec{r})\ i\vec{q}u_n*(\vec{k},\vec{r})\,u_1(\vec{q},\vec{r})\,d^3r\ +$$
$$\int \exp(i[\vec{q} + \vec{s}0 - \vec{k}].\ \vec{r})\,u_n*(\vec{k},\vec{r})\ \nabla u_1(\vec{q},\vec{r})\,d^3r \quad (8)$$

The functions ($u_n^*\ u1$) and ($u_n^*\nabla\ u_1$) are periodic .The electromagnetic wavelength is sufficiently large so that $\vec{k}$ and $\vec{q}$ are within the Brilloun zone. The integral over all space is separated into a sum over unit cells times an integral over a single unit cell [34].
Therefore equation (8) can be written as

$$\langle n\vec{k}|\exp(i\vec{s}0\ .\vec{r})\nabla|l\bar{q}\rangle = \left[\frac{(2\pi)^3}{\Omega}\right]\ x$$
$$\{i\bar{q}\delta(\vec{q} + \vec{s}0 - \vec{k})\ \delta_{nl}(\vec{q} + \vec{s}0 - \vec{k})\ .$$
$$\int_{cell} u_n^*(\vec{k},\vec{r})\nabla u1(\vec{q},\vec{r})\,d^3r\}$$
$$=\left[\frac{(2\pi)^3}{\Omega}\right]\{\delta(\vec{q} + \vec{s}0 -$$
$$\vec{k})\ \int_{cell} u_n^*(\vec{k},\vec{r})\nabla u1(\vec{q},\vec{r})\,d^3r\} \quad (9)$$

Here Ω is the volume of the unit cell and $\int u_n^*(\vec{k},\vec{r})u1(\vec{q},\vec{r})\,d^3r = \delta(\vec{q} - \vec{k})$ δ_{nl} =0, since n and l are not equal. From equation (6) and (9) we can write

$$\overline{H'}_{nl} = \frac{eA_0}{2m_c}\vec{\varepsilon}_s.\ \overrightarrow{p_{nl}}(\vec{k})\ \delta(\vec{q} - \vec{k})\cos(\omega t) \quad (10)$$

Where $\bar{p}_{nl}(\vec{k}) = -i\bar{h}\int u_n^*\nabla u_l d^3r =$
$\int u_n^*(\vec{k},\vec{r})\,\vec{p}u_l(\vec{k},\vec{r})\,d^3r$

Therefore we have

$$\overline{H'}_{nl} = \frac{eA_0}{2m_c}\vec{\varepsilon}_s.\ \overrightarrow{p_{nl}}(\vec{k}) \quad (11)$$

We can neglect the transition of the electrons in the same band because of recombination process. So we may have, $\langle n\vec{k}|H'|n\vec{k}\rangle = 0$

The second order perturbed energy now can be written as

$$E_n^{(2)}(\vec{k}) = E_n(\vec{k}) + \langle n\vec{k}|\overline{H'}|n\vec{k}\rangle + \frac{|\langle n\vec{k}|\overline{H'}|l\vec{k}\rangle|^2}{E_n(\vec{k}) - E_l(\vec{k})} \quad (12)$$

With n=c (conduction band) and l=v (valance band), the energy equation for conduction electrons assumes the form

$$E_c^{(2)}(\vec{k}) = E_c(\vec{k}) + \frac{\left(\frac{eA_0}{2m_c}\right)^2\ |\overrightarrow{\varepsilon_s}.\ \overrightarrow{p_{cv}}(\vec{k})|^2}{E_c(\vec{k}) - E_v(\vec{k})} \quad (13)$$

Where $|\overrightarrow{\varepsilon_s}.\ \overrightarrow{p_{cv}}(\vec{k})|^2$ represents square of OME. According to three band model of Kane,

$$\xi 1k = E_c(\vec{k}) - E_v(\vec{k}) = \left(E_{g0}^2 + E_{g0}\,\overline{h^2}\,\frac{k^2}{m_x}\right)^{\frac{1}{2}} \quad (14)$$

$$\gamma(E) = \frac{\overline{h^2}\,k^2}{2m_c} \quad (15)$$

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and

$$\left(\frac{eA_0}{2m_c}\right)^2 \cdot \frac{\left|\overrightarrow{\varepsilon_s}\cdot\overrightarrow{p_{cv}}(\vec{k})\right|^2}{E_c(\vec{k})-E_v(\vec{k})} =$$

$$\left(\frac{eA_0}{2m_c}\right)^2 \frac{2\pi}{3}\left|\overrightarrow{\varepsilon_s}\cdot\overrightarrow{p_{cv}}(0)\right|^2 \frac{\beta^2}{4}\left(t+\frac{\rho}{\sqrt{2}}\right)^2 x$$

$$\frac{1}{\xi 1k}\left\{\left(1+\frac{E_{g-\delta'}}{\xi 1k+\delta'}\right)+\left(E_g-\delta'\right)\left[\frac{1}{\xi 1k+\delta'}-\frac{1}{E_g+\delta'}\right]^{\frac{1}{2}} x \left[\frac{1}{\xi 1k+\delta'}-\frac{E_g+\delta'}{(E_g-\delta')^2}\right]^{\frac{1}{2}}\right\}^2 \quad (16)$$

In which E_{g0} is the unperturbed band gap, m_r is the reduced mass given by $m_r^{-1}=m_c^{-1}+m_v^{-1}$, m_v is the effective mass of heavy hole, $\gamma(E)=E(aE+1)(bE+1)/(cE+1)$, $a=E_{g0}^{-1}$, $b=(E_{g0}+\Delta)^{-1}$, Δ is the spin orbit splitting factor and $c=(E_{g0}+2\Delta/3)^{-1}$.

Following the perturbation theory and using appropriate equations we can write

$$\gamma(E)=\frac{\overline{h^2}\,k^2}{2m_c}+\left(\frac{eA_0}{2m_c}\right)^2 \frac{2\pi}{3}\left|\overrightarrow{\varepsilon_s}\cdot\overrightarrow{p_{cv}}(0)\right|^2 \frac{\beta^2}{4}\left(t+\frac{\rho}{\sqrt{2}}\right)^2 x \frac{1}{\xi 1k}\left\{\left(1+\frac{E_{g-\delta'}}{\xi 1k+\delta'}\right)+\left(E_g-\delta'\right)\left[\frac{1}{\xi 1k+\delta'}-\frac{1}{E_g+\delta'}\right]^{\frac{1}{2}} x \left[\frac{1}{\xi 1k+\delta'}-\frac{E_g+\delta'}{(E_g-\delta')^2}\right]^{\frac{1}{2}}\right\}^2$$

It can be shown that [30],

$$\chi_0^2=\frac{I\lambda^2}{2\pi^2 c^3\sqrt{\epsilon\epsilon_0}} \quad (17)$$

Where I is the light intensity of wavelength λ, c is the velocity of light, ϵ is the permittivity of semiconductor and ϵ_0 is the permittivity of vacuum. Thus the simplified electron energy spectrum in III-V, ternary materials like *n-$Hg_{1-x}Cd_xTe$* in the presence of light waves can be expressed as

$$\frac{\overline{h^2}\,k^2}{2m_c}=\beta_0(E,\lambda) \quad (18)$$

Where, $\beta_0(E,\lambda)=\gamma(E)-\theta_0(E,\lambda)$ (19)

$$\theta_0(E,\lambda)=\frac{e^2}{48m_x\pi c^3}\frac{I\lambda^2}{\sqrt{\epsilon\epsilon_0}}\frac{E_{g0}\left(E_{g0}+\Delta\right)}{\left(E_{g0}+\left(\frac{2}{3}\right)\Delta\right)}\frac{\beta^2}{4} x \left(t+\frac{\rho}{\sqrt{2}}\right)^2 \frac{1}{\emptyset_{0(E)}}\left\{\left(1+\frac{E_{g0}-\delta'}{\emptyset_{0(E)+\delta'}}\right)+\left(E_{g0}-\delta'\right)\left[\frac{1}{\emptyset_{0(E)+\delta'}}-\frac{1}{E_{g0}+\delta'}\right]^{1/2} x \left[\frac{1}{\emptyset_{0(E)+\delta'}}-\frac{E_{g0}+\delta'}{(E_{g0}-\delta')^2}\right]^{1/2}\right\}^2 \quad (20)$$

And

$$\emptyset_0(E)=E_{g0}\left(1+2\left(1+\frac{m_c}{m_v}\right)\frac{\gamma(E)}{E_{g0}}\right)^{1/2} \quad (21)$$

Thus under the limiting condition $\vec{k}\to 0$, from equation (18), we observe that $E\neq 0$ and is positive. Therefore , the energy of the electron does not tend to zero when $\vec{k}\to 0$, whereas for the un-perturbed three-band model of Kane, $\gamma(E)=\frac{\overline{h^2}\,k^2}{2m_c}$ in which $E\to 0$ for $\vec{k}\to 0$. Therefore this will provide the increased band gap(ΔE_g) of the semiconductor due to photon excitation. The values of the increased band gap can be obtained for various values of I and λ. This implies that when a semiconductor is exposed to a light wave, band gap gets perturbed with an increased band gap depending on the intensity of light and the color of light wave.

Special cases

1. For the two-band model of Kane, we have $\Delta\to 0$. Under this case, $\gamma(E)\to E(1+\alpha E)=\frac{\overline{h^2}\,k^2}{2m_c}$ with $\alpha=1/E_{g0}$. Since $\beta\to 1$, $t\to 1$, $\rho\to 0$, $\delta'\to 0$ for $\Delta\to 0$, from equation (18), we can write the energy spectrum for *n-$Hg_{1-x}Cd_xTe$* materials in the presence of external photo-excitation whose unperturbed conduction electrons obey the two-band model of Kane as

$$\frac{\overline{h^2}\,k^2}{2m_c}=\omega_0(E,\lambda) \quad (22)$$

Where $\omega_0(E,\lambda)=E(1+\alpha E)-B_0(E,\lambda)$

$$B_0(E,\lambda)=\frac{e^2 I\lambda^2 E_{g0}}{192\pi c^3 m_x\sqrt{\epsilon\epsilon_0}}\frac{1}{\emptyset_{1(E)}}\left\{\left(1+\frac{E_{g0}}{\emptyset_{1(E)}}\right)+E_{g0}\left[\frac{1}{\emptyset_{1(E)}}-\frac{1}{E_{g0}}\right]\right\}^2$$

$$\emptyset_{1(E)}=E_{g0}\left\{1+\frac{2m_c}{m_x}\frac{E(1+\alpha E)}{E_{g0}}\right\}^{1/2}$$

2.When the unperturbed conduction band is approximated by the parabolic electron energy spectrum, we can write $a\to 0$, $b\to 0$, $c\to 0$ and , $\gamma(E)\to E$. Thus , again from equation (18),

$$\frac{\overline{h^2}\,k^2}{2m_c}=\rho_0(E,\lambda) \quad (23)$$

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$$\rho_0(\mathrm{E})=\mathrm{E}-\frac{e^2 I\lambda^2}{48\pi c^3 m_x\sqrt{\epsilon\epsilon_0}} \quad (24)$$

EMM in the presence of light wave in n-$Hg_{1-x}Cd_xTe$

The effective momentum mass can be written as[3]

$$m^*(\mathrm{E_F})=[(\bar{h}k)/(\frac{1}{\bar{h}}\frac{\delta E}{\delta k})]|_{E=E_F}=\overline{h^2}k\frac{\delta k}{\delta E}|_{E=E_F} \quad (25)$$

Using (18) & (25) we have

$$m^*(\mathrm{E_F})=\mathrm{m_c}[\gamma'(E_F)-\theta_0'(E_F,\lambda)] \quad (26)$$

Where symbols with prime indicate differentiation with respect to E_F. Thus EMM requires electron statistics which comes from density of states function. Using (18) the DOS for *n-$Hg_{1-x}Cd_xTe$* in presence of light wave can be expressed as

$$\mathrm{D_0(E)}=4\pi\left(\frac{2\mathrm{mc}}{h^2}\right)^{\frac{3}{2}}\sqrt{\beta 0(\mathrm{E},\lambda)}\,\beta_0'(\mathrm{E},\lambda) \quad (27)$$

Where $\beta_0'(\mathrm{E},\lambda)=\frac{\delta}{\delta \mathrm{E}}[\beta 0(\mathrm{E},\lambda)]$

Applying Fermi-Dirac occupancy probability on (27) and using the concept of generalized Somerfield's lemma [30], the electron concentration is expressed as

$$\mathrm{n_0}=(3\pi^2)^{-1}\left(\frac{2\mathrm{mc}}{\bar{h}^2}\right)^{\frac{3}{2}}[\mathrm{M_1}(E_F,\lambda)+\mathrm{N_1}(E_F,\lambda)] \quad (28)$$

where,

$$\mathrm{M_1}(E_F,\lambda)\equiv[\beta_0(E_F,\lambda)]^{3/2}$$
$$\mathrm{N_1}(E_F,\lambda)=\sum_{r=1}^{S'}L(r,0)\mathrm{M1}(E_F,\lambda)$$
$$\mathrm{L(r,J)}\equiv[2(k_B T)^{2r}(1\text{-}2^{1-2r})\xi(2r)]\left[\frac{\partial^{2r+J}}{\partial E_F^{2r+J}}\right]$$

Again r, J is the sets of real positive integers and ξ (2r) is the ξ function of order 2r[52].

Now expression of EMM and n_0 for *n-$Hg_{1-x}Cd_xTe$* in presence of light wave whose unperturbed conduction electrons obey the two band model of Kane can be expressed as

$$m^*(\mathrm{E_F})=\mathrm{m_c}[(1+2\alpha E_F)-B_0'(E_F,\lambda)] \quad (29)$$

$$\mathrm{n_0}=(3\pi^2)^{-1}\left(\frac{2\mathrm{mc}}{\bar{h}^2}\right)^{\frac{3}{2}}[\mathrm{M_2}(E_F,\lambda)+\mathrm{N_2}(E_F,\lambda)] \quad (30)$$

where $\mathrm{M_2}(E_F,\lambda)\equiv[\omega_0(E_F,\lambda)]^{3/2}$ and $\mathrm{N_2}(E_F,\lambda)=\sum_{r=1}^{S'}L(r,0)\,\mathrm{M_2}(E_F,\lambda)$

EMM in the absence of light wave in n-$Hg_{1-x}Cd_xTe$

(A) According to the three band model of Kane the EMM and n_0 can be expressed as

$$m^*(E_{F_0})=\mathrm{m_c}[\gamma'(E_{F_0})] \quad (31)$$

$$\mathrm{n_0}=(3\pi^2)^{-1}\left(\frac{2\mathrm{mc}}{\bar{h}^2}\right)^{\frac{3}{2}}[\mathrm{M_4}(E_{F_0})+\mathrm{N_4}(E_{F_0})] \quad (32)$$

Where $\mathrm{M_4}(E_{F_0})\equiv[\gamma(E_{F_0})]^{3/2}$ and $\mathrm{N_4}(E_{F_0})=\sum_{r=1}^{S'}L(r,0)\,\mathrm{M_4}(E_{F_0})$

(B) With reference two band model of Kane thee expressions for EMM and n_0 are given by

$$m^*(E_{F_0})=\mathrm{m_c}[(1+2\alpha E_{F_0})] \quad (33)$$

$$\mathrm{n_0}=(3\pi^2)^{-1}\left(\frac{2\mathrm{mc}}{\bar{h}^2}\right)^{\frac{3}{2}}[\mathrm{M_5}(E_{F_0})+\mathrm{N_5}(E_{F_0})] \quad (34)$$

where $\mathrm{M_5}(E_{F_0})\equiv[E_{F_0}(1+2E_{F_0})]^{3/2}$ and $\mathrm{N_5}(E_{F_0})]=\sum_{r=1}^{S'}L(r,0)\,\mathrm{M_5}(E_{F_0})$

(c) As a special case with $\Delta>>E_{g0}$ or $\Delta<<E_{g0}$ together with the condition $\alpha E_{F_0}<<1$, equation (34) reduced to the form

$$\mathrm{n_0}=N_c\left[F_{\frac{1}{2}}(\eta)+\left(\frac{15\alpha k_B T}{4}\right)F_{\frac{3}{2}}(\eta)\right] \quad (35)$$

where $N_c=2(2\pi m_c k_B T/h^2)^{3/2}$, $\eta=E_{F_0}/k_B T$ and $F_t(\eta)$ is the one parameter Fermi-Dirac integral of order t_0 which can be written as [31]

$$F_{t0}(\eta)=\left(\frac{1}{\Gamma(t_0+1)}\right)\int_0^\infty y^{t0}(1+\exp(y-\eta))^{-1}\,\mathrm{dy}\quad,\ \mathrm{y>-1} \quad (36)$$

The Gamma function is complex here and continued as a complex contour integral towards the negative axis. So,

$$F_{t0}(\eta)=A_{t0}\int_{-\infty}^{0+}y^{t0}(1+\exp-y-\eta))^{-1}\,\mathrm{dy} \quad (37)$$

In which $A_{t0}=\Gamma(-t_0)/2\pi\sqrt{-1}$

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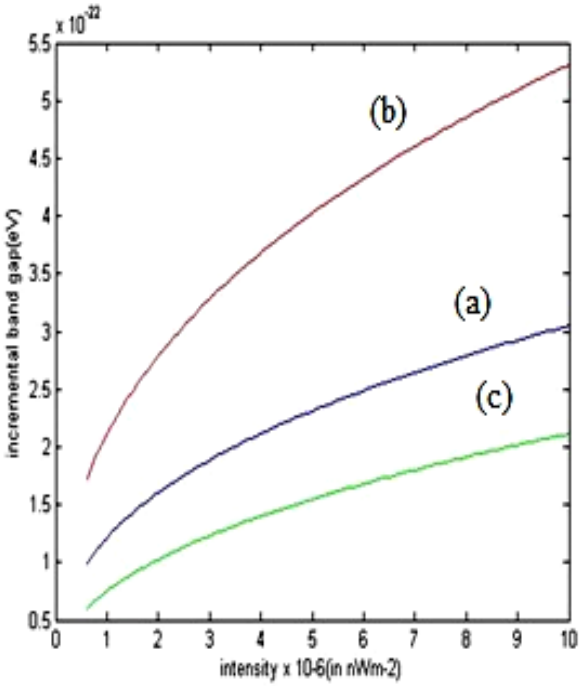
(D) Under the condition $E_g \rightarrow \infty$, we have the simplified results [31], given as

$$m^*(E_F) = m_c \, , \; n_0 = N_c \, F_{\frac{1}{2}}(\eta) \qquad (38)$$

III. Results and Discussions

Using the appropriate equations, we have plotted (figure 1) incremental band gap (ΔEg) of n-$Hg_{1-x}Cd_xTe$ as a function of I (for a given wavelength λ= 660 nm) at T = 4.2K in figure 1 using x = 0.2, m_v= 0.4m0, εr = 12.642,Δ = (0.063 + 0.24x + 0.27x2) eV, Eg_0 = [−0.302 + 1.93x +5.25×10^{-4} T(1−2x)−0.810x^2 + 0.832x^3] eV. In figure 2, we have plotted the increased band gap for the same semiconductors as a function of λ assuming I =10nWm $^{-2}$ for the purpose of numerical computations. In figure 3, and also in figure 4 we have plotted the EMM as functions of wavelength and electron concentration respectively.

The ΔEg increases with increasing I for both perturbed three and two band models of Kane and as well as with perturbed parabolic energy band models. We observed that for a given value of the intensity of light, when a semiconductor is exposed to different colors of light, the band gap of the semiconductor also increases with the wavelength of light although the rate of change is totally different as compared with the curves of figure 1. The influence of light is apparent from the plots in figures 3, since the EMM depends strongly on I and λ for the three- and the two-band model of Kane which is in direct contrast with that for the bulk specimens of said compounds in the absence of external photo-excitation. The variations of the EMM in figure 4 reflect the direct signature of the light wave on the band-structure dependent physical properties of semiconductors in general in the presence of external photo-excitation and the photon assisted transport for the corresponding photonic devices. The numerical values of the EMM in the presence of the light waves are larger than that of the same in the absence of light waves for both the three- and the two-band model of Kane. Although the EMM tends to increase with the intensity and the wavelength, the rate of increase is totally band-structure dependent. It appears that the numerical values of the EMM are greatest for ternary materials and least for quaternary compounds.



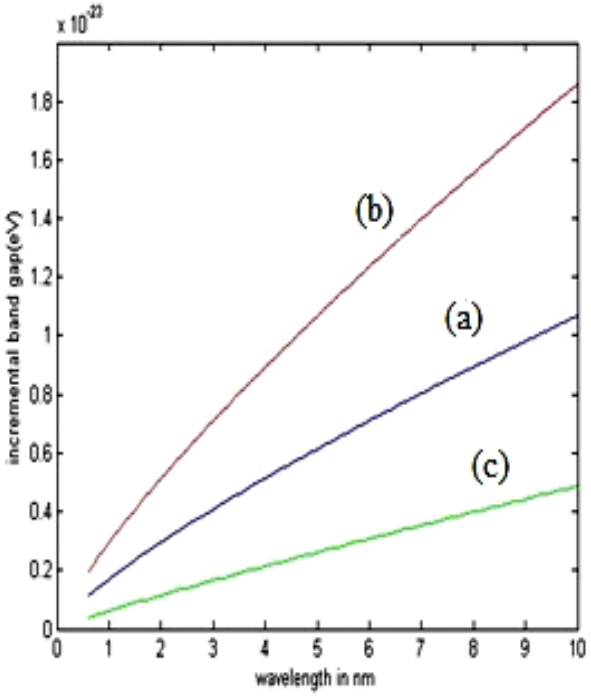


Figure 1 & 2 : (a) and (b) represent the variations according to perturbed three- and two-band models of Kane respectively. The curve (c) represents the same variation in n-Hg1−xCdxTe in accordance with the perturbed parabolic energy bands

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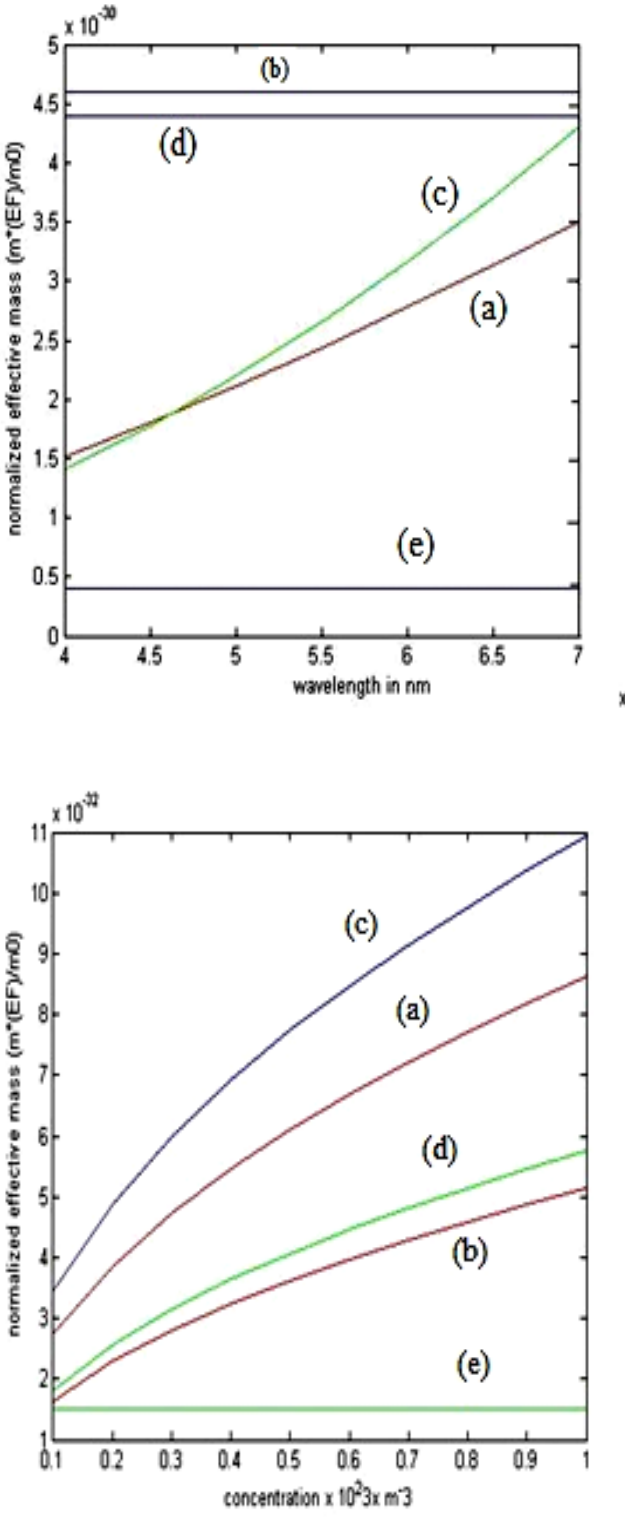

Figure 3 & 4 :EMM n-Hg1−xCdxTe in the presence of light waves in which the curves (a) and (c) represent the three- and two-band models of Kane respectively. The curves (b) and (d) exhibit the same variation in the absence of external photo-excitation. The curve (e) represents the parabolic energy band model both in the presence and in the absence of the external photo-excitation.

The theoretical results of our paper will be useful in determining the mobility, even for relatively wide gap compounds whose energy band structures can be approximated by the parabolic energy bands, both in the presence and absence of light waves. It is worth remarking that our basic equations (20-24), cover various materials with different energy band structures. In this paper, the concentration, alloy composition, light intensity and the wavelength dependences of the EMM for *n-$Hg_{1-x}Cd_xTe$* lattice matched to InP have been studied. Thus, we have covered a class of optoelectronic and allied compounds whose energy band structures are defined by the three- and two-band models of Kane in the absence of photon field. This analysis not only shows the mathematical compatibility of our formulation but also shows the fact that our discussion is a more generalized one, since one can obtain the corresponding results for the relatively wide gap materials having parabolic energy bands under certain limiting conditions from our present derivation.

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Anirban Neogi, He is currently working as the HOD of ECE department of Dr. Sudhir Chandra Sur Degree Engineering College.She has started her carrier as a lecturer in Bengal Institute of Technology (Under Techno India Group). He has total experience of over 10 years in teaching. As a part of his research activity he got 6 international journal publications and few conference papers in the field of Nanoscience and as well as in Ad-hoc network. He did his M.Tech from Institute of Radio Physics and Electronics and M.Sc. in Electronic Science from university college of science and technology, Calcutta university..

Manali Dhar, Assistant Professor, Department of ECE, B.Tech (Electronics & communication Engineering), M.Tech (Microelectronics & VLSI Design), 2 national conference, one national seminar paper publications. Research area is VLSI, Semiconductor devices.

Dr.(Prof) Amit Kumar Aditya, Is the former principal of Asansole Engineering College and currently working as a Director of Dr Sudhir Chandra Sur Degree Engineering College. He is a ex student of JU (B.Tech), and Kharagpur IIT(M.Tech and P.hd.).

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